

**SUPPLEMENTAL AMENDMENT
U.S. Appln. No. 09/900,962****Attorney Docket Q61744**

producing a catalyst layer comprising a metal, alloy or metallic compound containing at least one element selected from the group consisting of Ni, Co, Fe, Mn, Cr, V, Ti, Re, W, Ta, Hf, Lu, Gd, Ce, La, Ru, Mo, Zr, Y, Au, Ag, Cu, Al and Bi on said gallium nitride-compound semiconductor layer;

annealing the gallium nitride-based compound semiconductor layer fixed with said catalyst layer in an atmosphere gas containing no oxygen;

stripping said catalyst layer completely; and

providing a p-side electrode on said p-type layer after annealing.

10. (amended) The method for producing a gallium nitride-based compound semiconductor light-emitting device as claimed in claim 9, wherein said catalyst layer is a monolayer or multilayer film.